



SPC6601

N & P Pair Enhancement Mode MOSFET

DESCRIPTION

The SPC6601 is the N- and P-Channel enhancement mode power field effect transistors are produced using high cell density , DMOS trench technology. This high density process is especially tailored to minimize on-state resistance and provide superior switching performance. These devices are particularly suited for low voltage applications such as notebook computer power management and other battery powered circuits where high-side switching , low in-line power loss, and resistance to transients are needed.

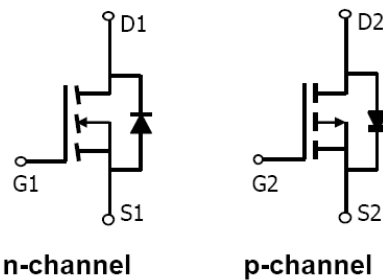
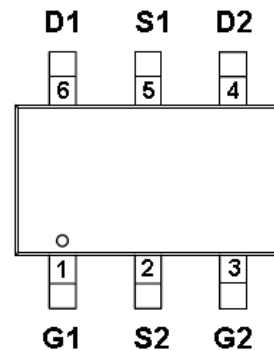
FEATURES

- ◆ N-Channel
 - 30V/2.8A,RDS(ON)= 68mΩ@VGS=10V
 - 30V/2.3A,RDS(ON)= 78mΩ@VGS=4.5V
 - 30V/1.5A,RDS(ON)= 108mΩ@VGS=2.5V
- ◆ P-Channel
 - 30V/-2.8A,RDS(ON)=105mΩ@VGS=-10V
 - 30V/-2.5A,RDS(ON)=120mΩ@VGS=-4.5V
 - 30V/-1.5A,RDS(ON)=148mΩ@VGS=-2.5V
- ◆ Super high density cell design for extremely low RDS (ON)
- ◆ Exceptional on-resistance and maximum DC current capability
- ◆ TSOT– 23-6P package design

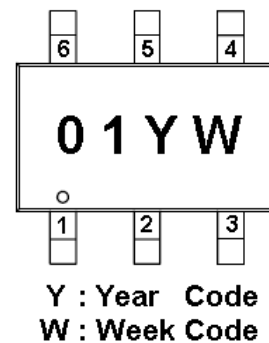
APPLICATIONS

- Power Management in Note book
- Portable Equipment
- Battery Powered System
- DC/DC Converter
- Load Switch
- DSC
- LCD Display inverter

PIN CONFIGURATION(TSOT– 23-6P)



PART MARKING





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PIN DESCRIPTION

Pin	Symbol	Description
1	G1	Gate 1
2	S2	Source 2
3	G2	Gate 2
4	D2	Drain 2
5	S1	Source 1
6	D1	Drain1

ORDERING INFORMATION

Part Number	Package	Part Marking
SPC6601TS26RGB	TSOT- 23-6P	01YW

※ Week Code : A ~ Z(1 ~ 26) ; a ~ z(27 ~ 52)

※ SPC6601TS26RGB : Tape Reel ; Pb – Free ; Halogen -Free

ABSOLUTE MAXIMUM RATINGS

(TA=25°C Unless otherwise noted)

Parameter	Symbol	Typical		Unit	
		N-Channel	P-Channel		
Drain-Source Voltage	V _{DSS}	30	-30	V	
Gate –Source Voltage	V _{GSS}	±12	±12	V	
Continuous Drain Current(T _J =150°C)	I _D	T _A =25°C	2.8	-2.8	A
		T _A =70°C	2.3	-2.1	
Pulsed Drain Current	I _{DM}	10	-8	A	
Continuous Source Current(Diode Conduction)	I _S	1.25	-1.4	A	
Power Dissipation	P _D	T _A =25°C	1.15		W
		T _A =70°C	0.75		
Operating Junction Temperature	T _J	-55/150		°C	
Storage Temperature Range	T _{STG}	-55/150		°C	
Thermal Resistance-Junction to Ambient	R _{θJA}	T ≤ 10sec	50	52	°C/W
		Steady State	90	90	



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ELECTRICAL CHARACTERISTICS

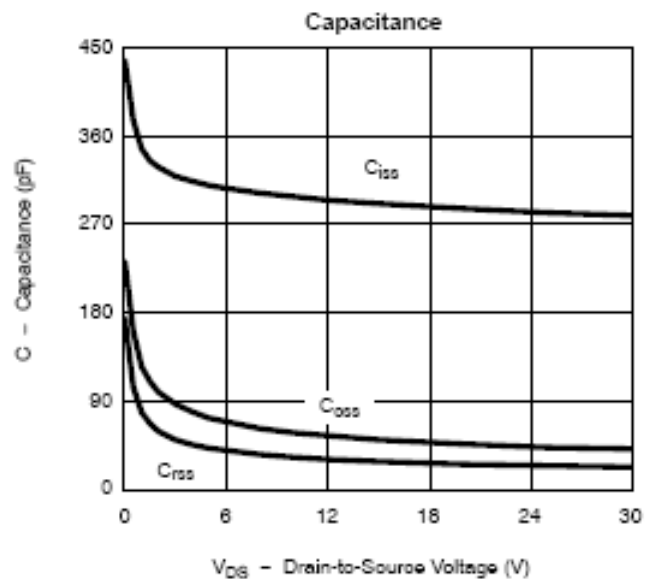
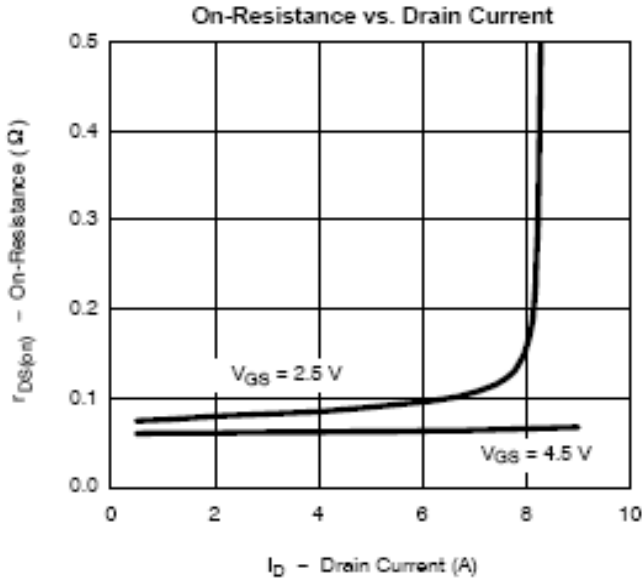
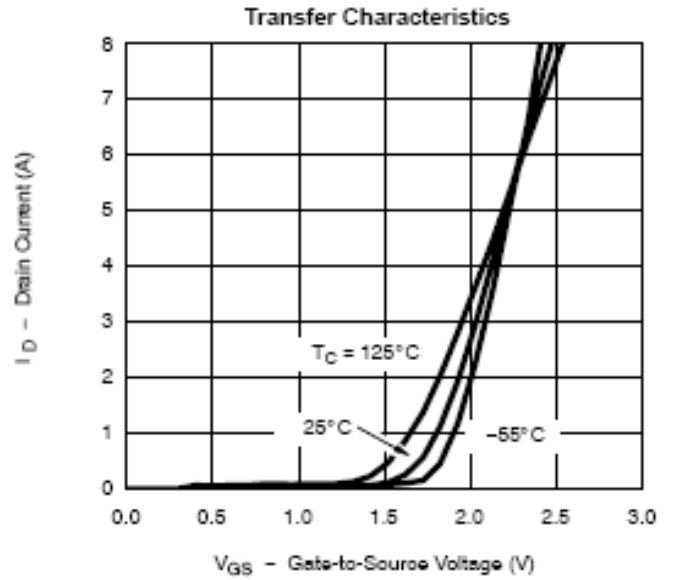
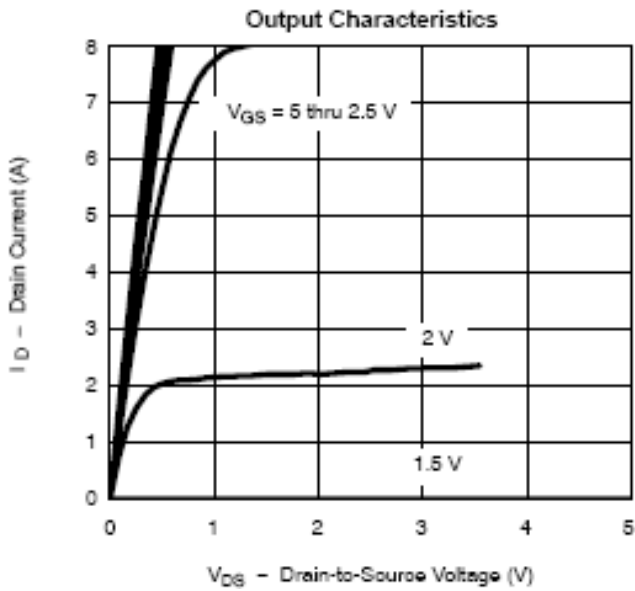
(TA=25°C Unless otherwise noted)

Parameter	Symbol	Conditions	Min.	Typ	Max.	Unit	
Static							
Drain-Source Breakdown Voltage	V _{(BR)DSS}	V _{GS} =0V, I _D = 250uA	N-Ch	30		V	
		V _{GS} =0V, I _D =-250uA	P-Ch	-30			
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} , I _D =250uA	N-Ch	0.8	1.6		
		V _{DS} =V _{GS} , I _D =-250uA	P-Ch	-0.4	-1.0		
Gate Leakage Current	I _{GSS}	V _{DS} =0V, V _{GS} =±12V	N-Ch		±100	nA	
		V _{DS} =0V, V _{GS} =±12V	P-Ch		±100		
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = 21V, V _{GS} =0V	N-Ch		1	uA	
		V _{DS} =-21V, V _{GS} =0V	P-Ch		-1		
		V _{DS} = 21V, V _{GS} =0V T _J =55°C	N-Ch		10		
		V _{DS} =-21V, V _{GS} =0V T _J =55°C	P-Ch		-10		
On-State Drain Current	I _{D(on)}	V _{DS} ≥ 5V, V _{GS} = 10V	N-Ch	6		A	
		V _{DS} ≤ -5V, V _{GS} = -10V	P-Ch	-6			
Drain-Source On-Resistance	R _{DS(on)}	V _{GS} = 10V, I _D = 2.8A	N-Ch		0.048	0.068	Ω
		V _{GS} =-10V, I _D =-2.8A	P-Ch		0.077	0.105	
		V _{GS} = 4.5V, I _D = 2.3A	N-Ch		0.054	0.078	
		V _{GS} =-4.5V, I _D =-2.5A	P-Ch		0.092	0.120	
		V _{GS} = 2.5V, I _D = 1.5A	N-Ch		0.079	0.108	
		V _{GS} =-2.5V, I _D =-1.5A	P-Ch		0.118	0.148	
Forward Transconductance	g _{fs}	V _{DS} =4.5V, I _D =2.8A	N-Ch		4.6	S	
		V _{DS} =-10V, I _D =-2.8A	P-Ch		4		
Diode Forward Voltage	V _{SD}	I _S = 1.25A, V _{GS} =0V	N-Ch		0.8	1.2	V
		I _S =-1.2A, V _{GS} =0V	P-Ch		-0.8	-1.2	
Dynamic							
Total Gate Charge	Q _g	N-Channel V _{DS} =15 , V _{GS} =4.5V , I _D ≐2.0A P-Channel V _{DS} =-15V , V _{GS} =-4.5V , I _D ≐-2.0A	N-Ch		4.2	6	nC
Gate-Source Charge	Q _{gs}		P-Ch		5.8		
			N-Ch		0.6		
Gate-Drain Charge	Q _{gd}		P-Ch		0.8		
			N-Ch		1.5		
Turn-On Time	t _{d(on)}		N-Ch		2.5		
		P-Ch		6			
	t _r	N-Ch		2.5			
		P-Ch		3.9			
Turn-Off Time	t _{d(off)}	N-Ch		20			
		P-Ch		40			
	t _f	N-Ch		4			
		P-Ch		15			



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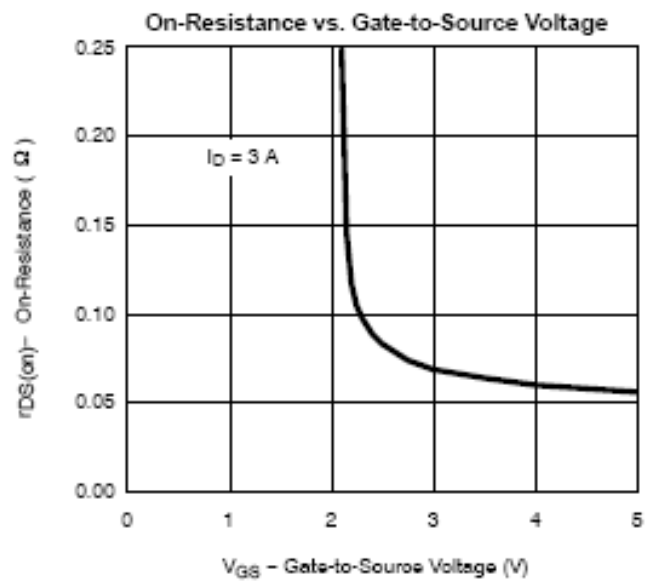
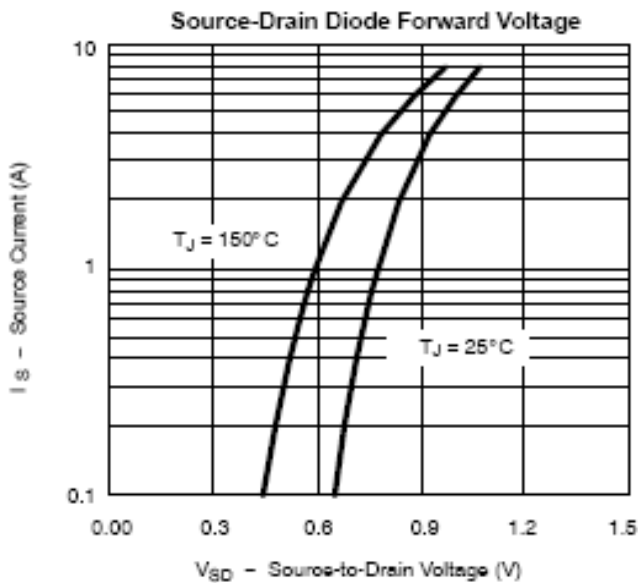
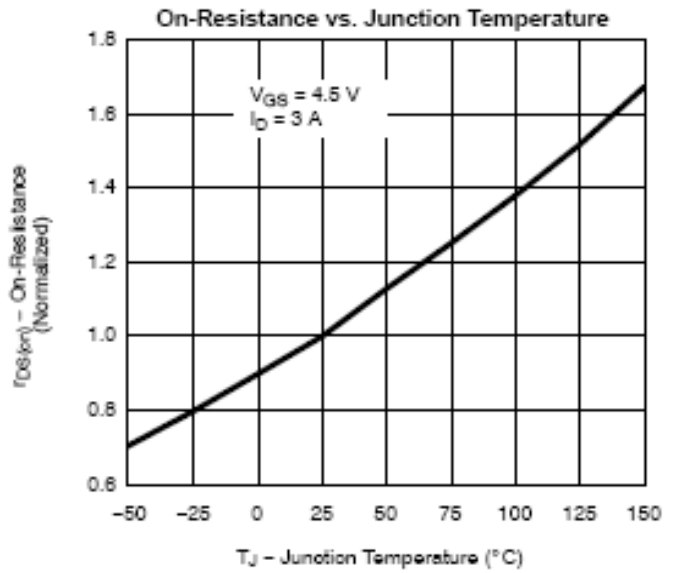
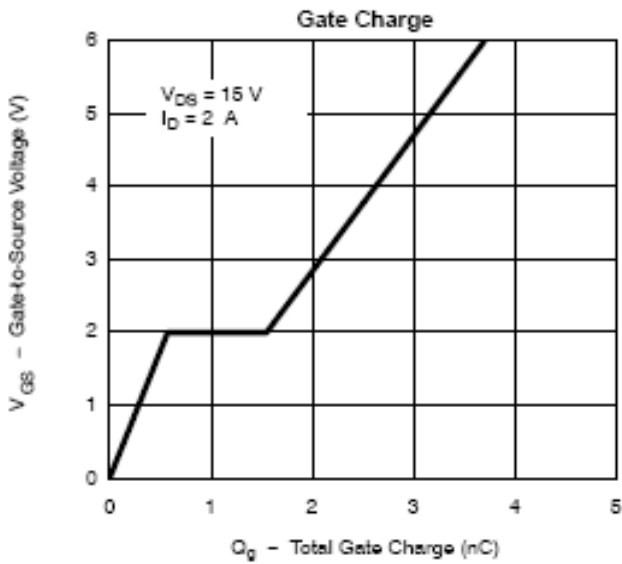
TYPICAL CHARACTERISTICS (N-Channel)





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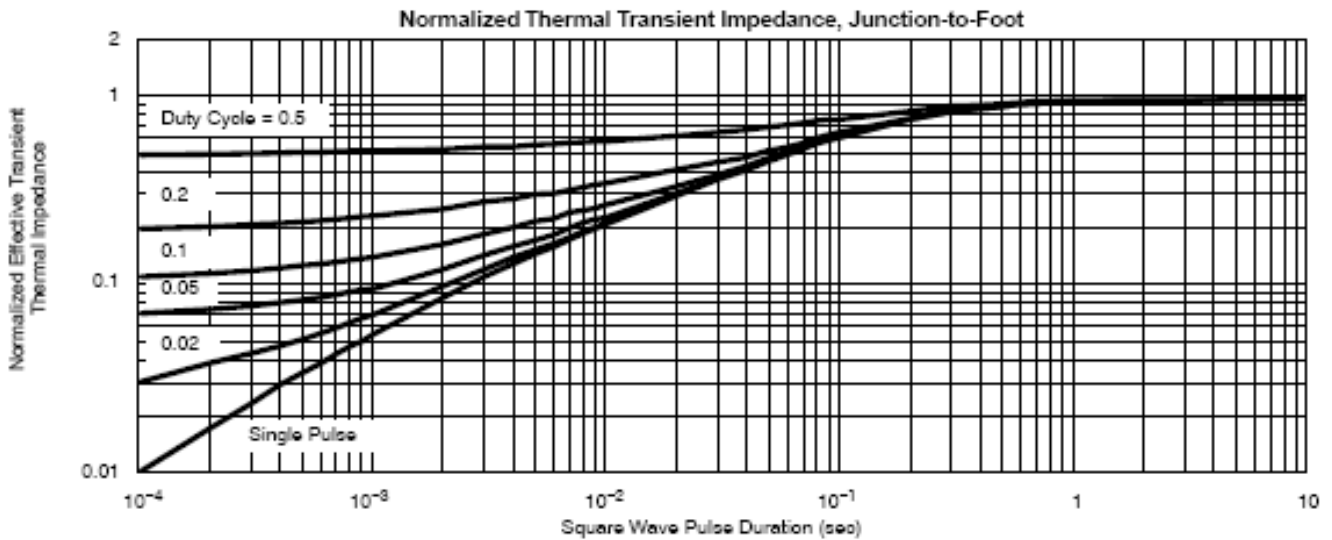
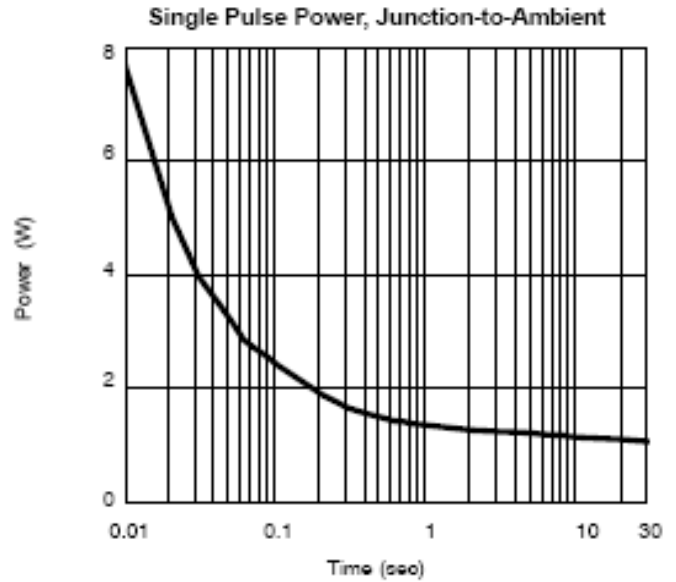
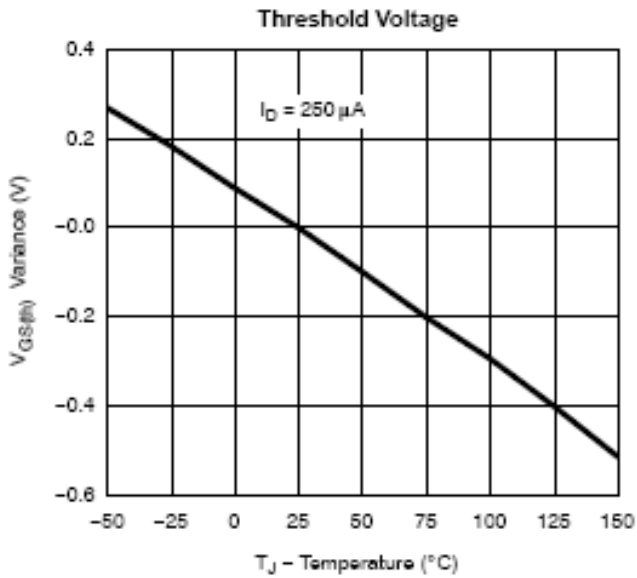
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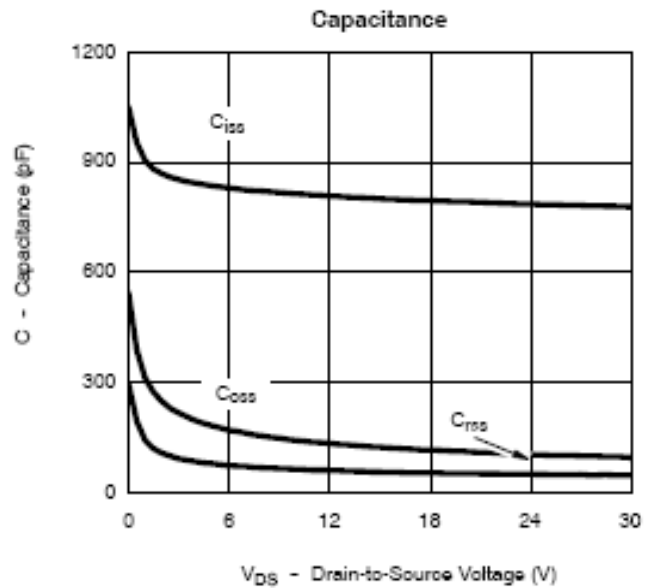
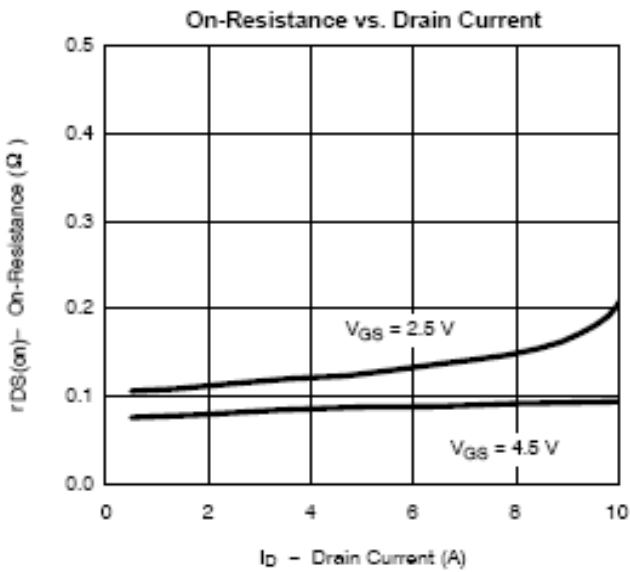
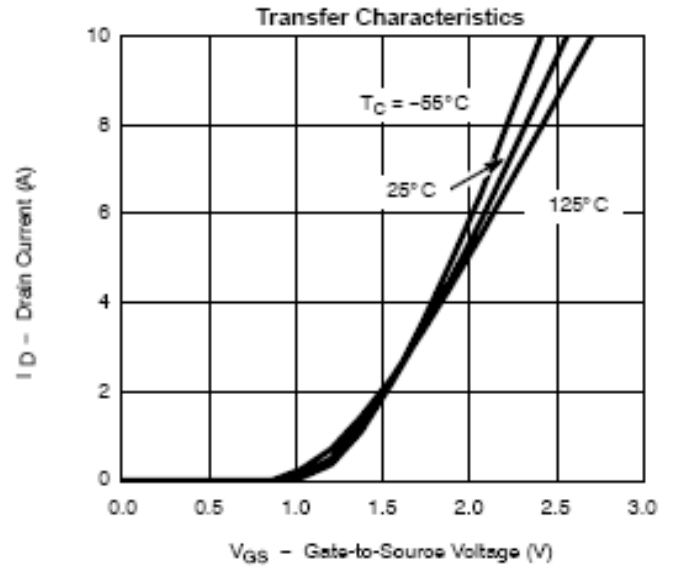
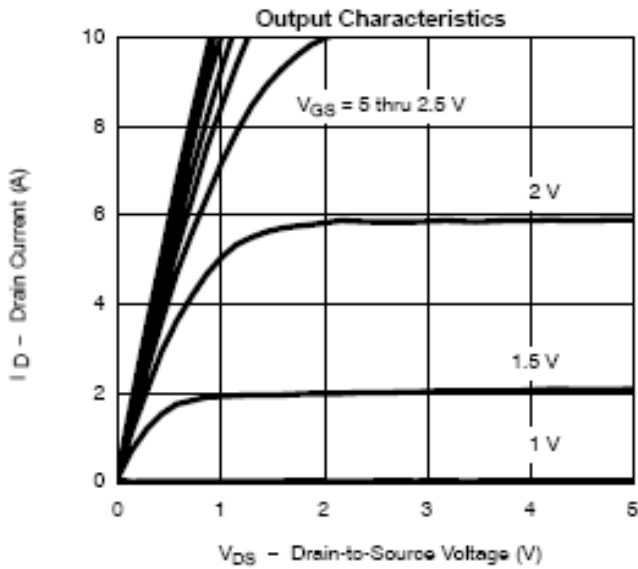




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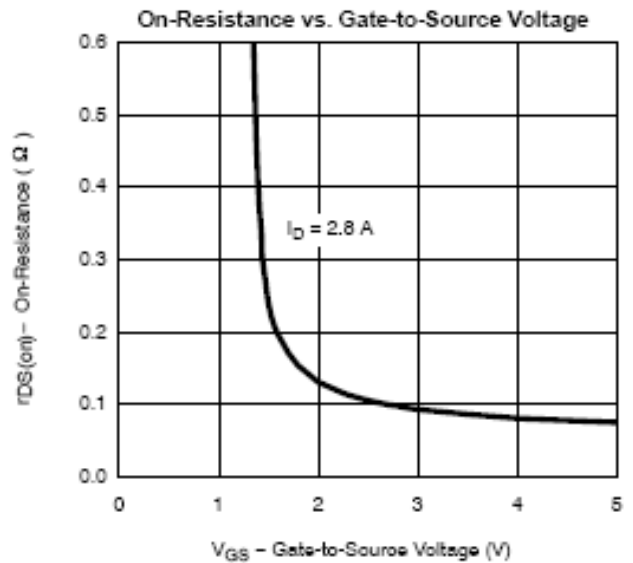
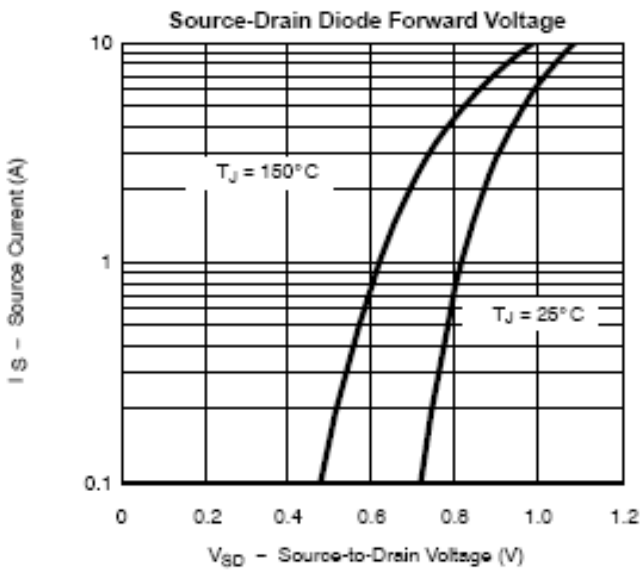
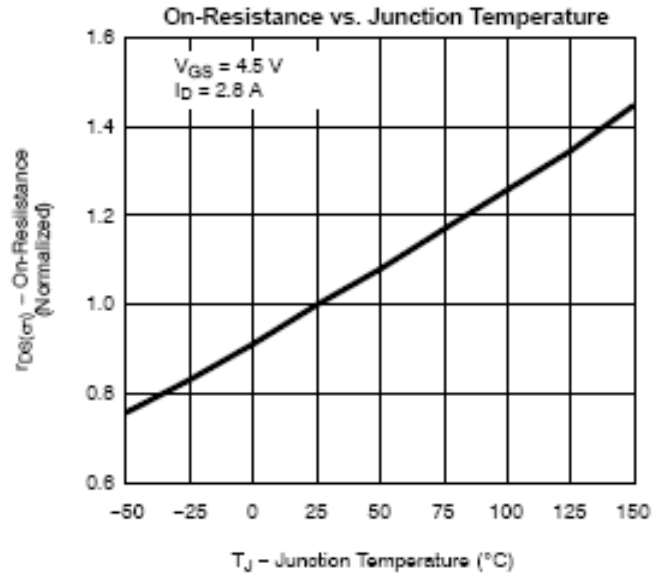
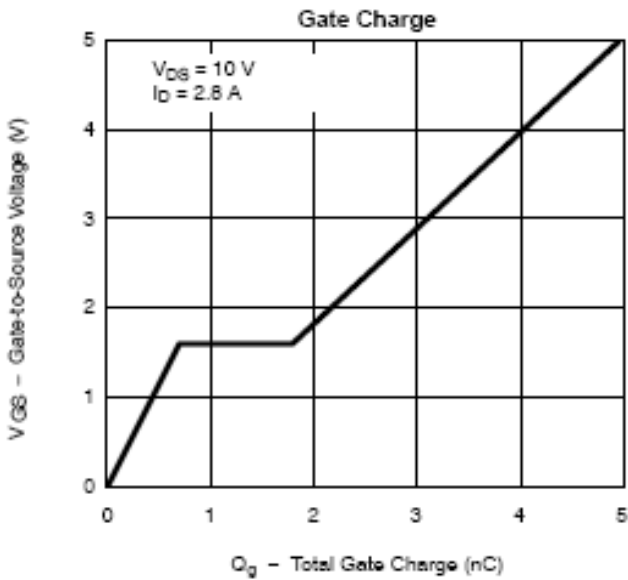
TYPICAL CHARACTERISTICS (P-Channel)





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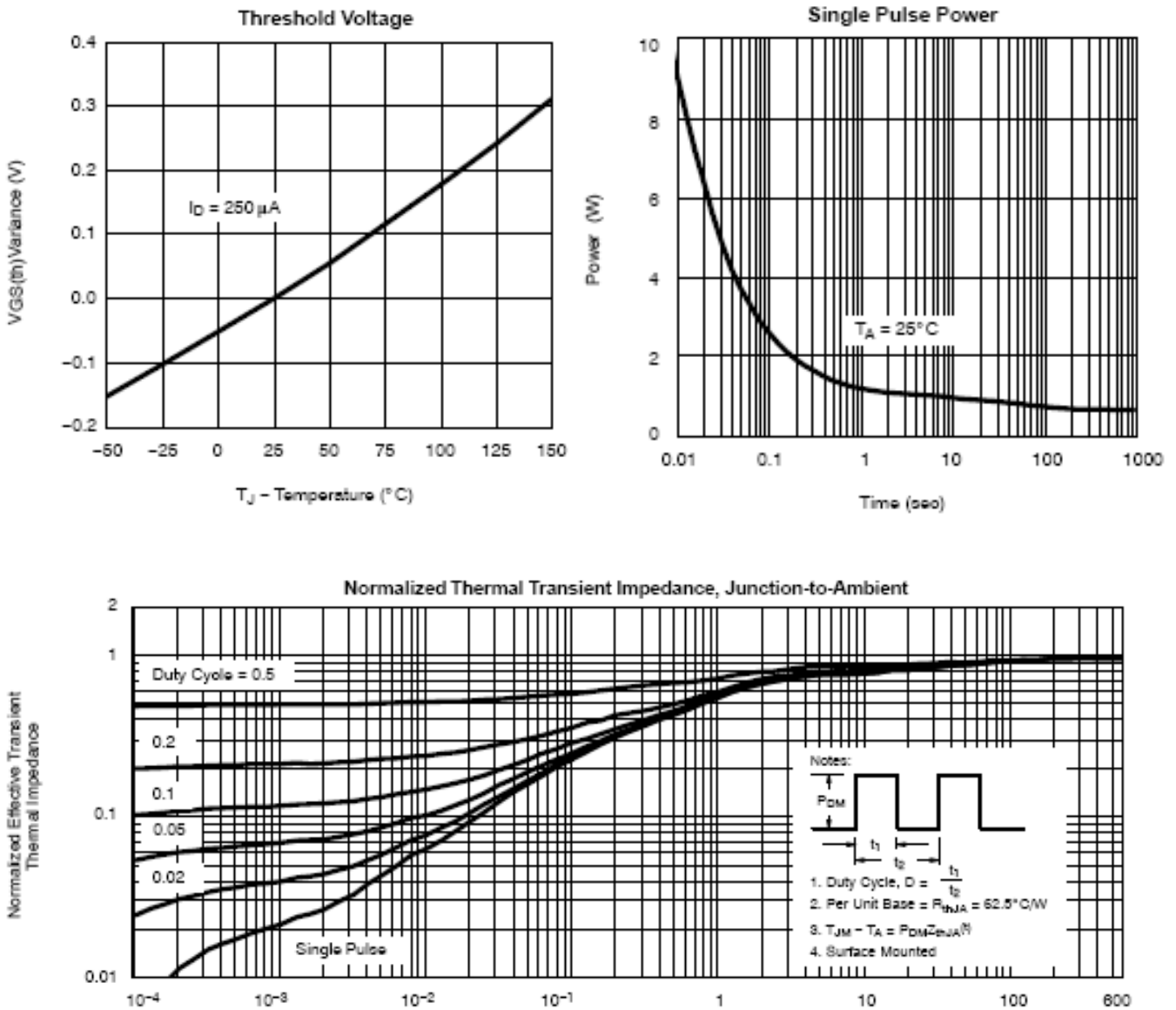
TYPICAL CHARACTERISTICS (P-Channel)





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TYPICAL CHARACTERISTICS (P-Channel)

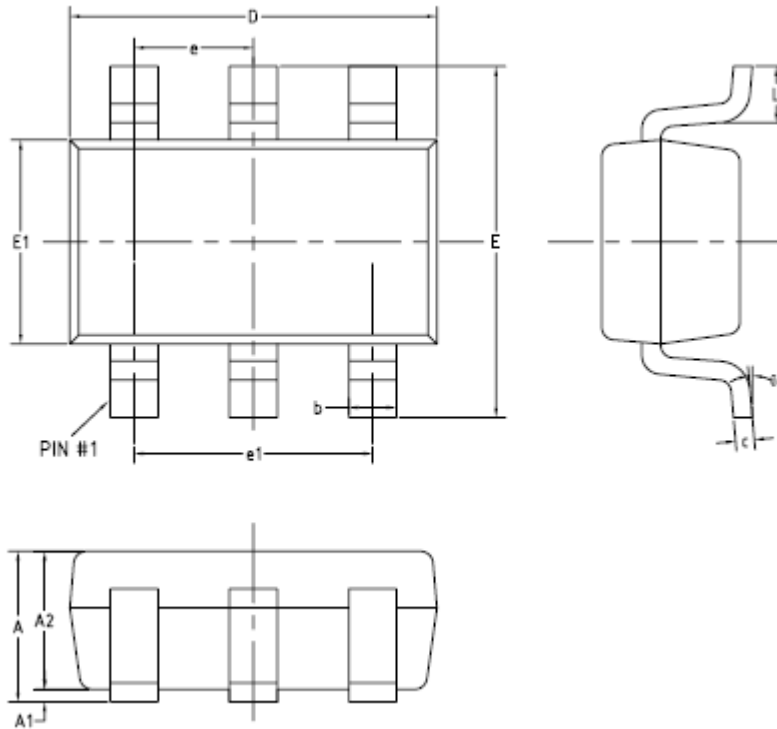




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TSOT-23- 6P PACKAGE OUTLINE



COMMON DIMENSIONS
(UNITS OF MEASURE=MILLIMETER)

SYMBOL	MIN	NOM	MAX
A	0.70	—	0.90
A1	0	—	0.10
A2	0.70	0.75	0.80
b	0.35	—	0.50
c	0.08	—	0.20
D	2.82	2.92	3.02
E	2.65	2.80	2.95
E1	1.60	1.65	1.70
e	0.95(BSC)		
e1	1.90(BSC)		
L	0.30	0.40	0.60
L1	0.59REF		
L2	0.25BSC		
θ	0°	—	8°



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